

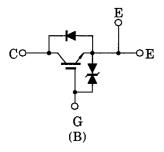
TOSHIBA GTR Module Silicon N Channel IGBT

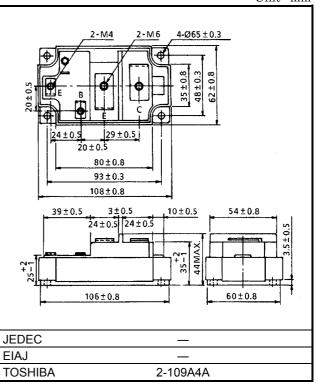
# MG200Q1US41

High Power Switching Applications Motor Control Applications

- High input impedance
- High speed :  $t_f = 0.5 \mu s$  (Max.)  $t_{rr} = 0.5 \mu s$  (Max.)
- Low saturation voltage
- $: V_{CE} (sat) = 4.0V (Max.)$
- Enhancement-mode
- The electrodes are isolated from case.

### **Equivalent Circuit**





Weight: 465g

### Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ι <sub>C</sub>	200	Α	
	1ms	I <sub>CP</sub>	400	~	
Forward current	DC	١ <sub>F</sub>	200	A	
	1ms	I <sub>FM</sub>	400		
Collector power dissipation (Tc = 25°C)		P <sub>C</sub>	1400	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC, 1 min.)	V	
Screw torque (Terminal : M4/M6 / mounting)		_	2/3/3	N∙m	

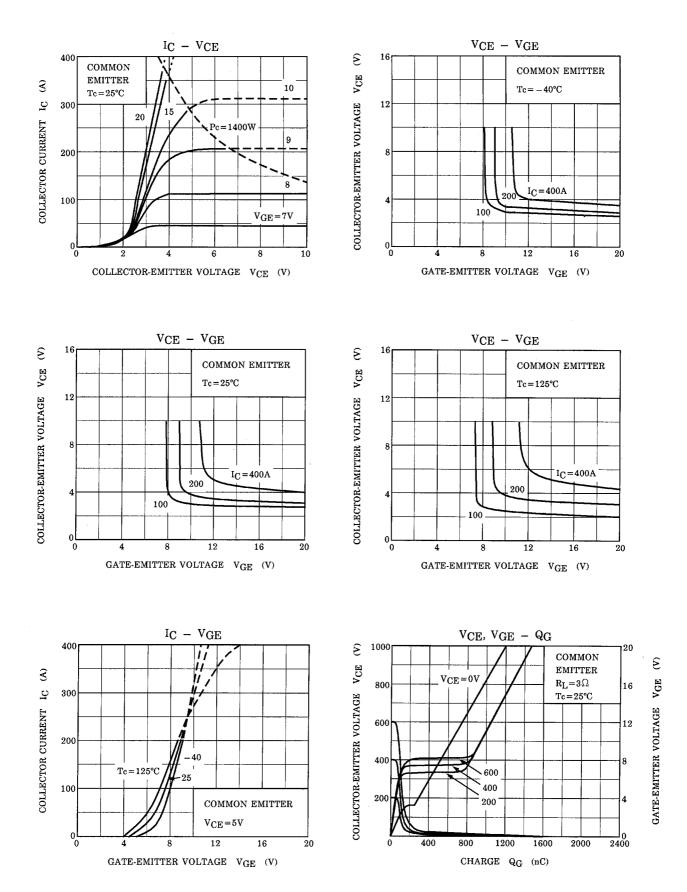
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Unit: mm

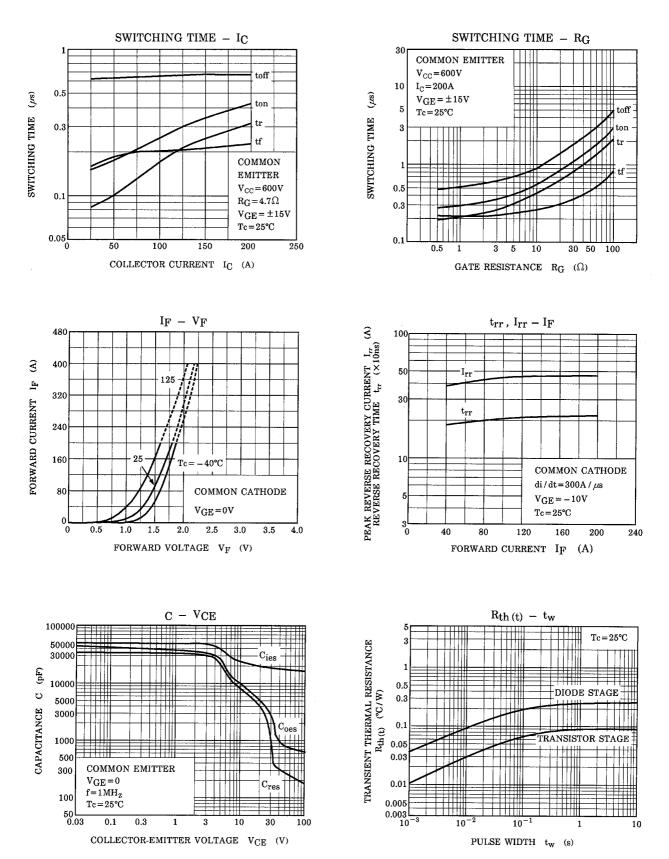
Electrical Characteristics (Ta = 25°C)

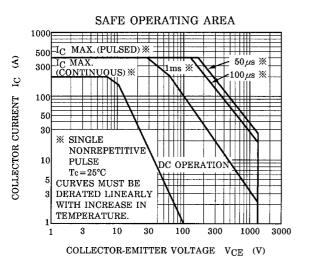
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE}$ = ±20V, $V_{CE}$ = 0	_	_	±40	μA
Collector cut-off current		ICES	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0		_	4.0	mA
Gate-emitter cut-off voltage		V <sub>GE (OFF)</sub>	I <sub>C</sub> = 200mA ,V <sub>CE</sub> = 5V	3.0	-	6.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V	_	3.0	4.0	V
Input capacitance		Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	_	24000	_	pF
Switching time	Rise time	tr	157	_	0.3	0.6	- µs
	Turn-on time	t <sub>on</sub>			0.4	0.8	
	Fall time	t <sub>f</sub>	$\square_{-15V}$		0.2	0.5	
	Turn-off time	t <sub>off</sub>	600V	_	0.8	1.5	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 200A, V <sub>GE</sub> = 0		2.0	3.0	V
Reverse recovery time		t <sub>rr</sub>	I <sub>F</sub> = 200A, V <sub>GE</sub> = −10V di / dt = 300A / μs	_	0.25	0.5	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor	_	_	0.089	°C/W
			Diode		—	0.25	C/W

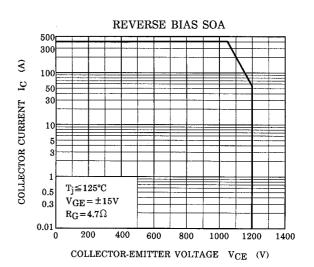
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